onsemi

N-Channel Power MOSFET

24 V, 9 A, 16 m Ω , Dual ECH8

ECH8655R-R-TL-H

Features

- Low ON-resistance
- 2.5 V Drive
- Common-drain Type
- Protection Diode in
- Built-in Gate Protection Resistor
- Best Suited for LiB Charging and Discharging Switch
- This Device is Pb-Free and are RoHS Compliant

Product & Package Information

• Package:

ECH8

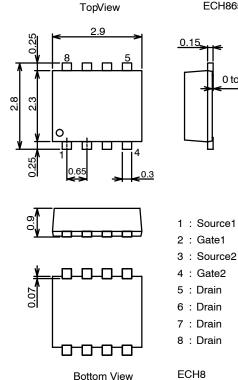
3,000 Pcs./Reel

- JEITA, JEDEC:
- Minimum Packing Quantity:

Unit : mm (typ) 7011A-003

ECH8655R-R-TL-H

0 to 0.02





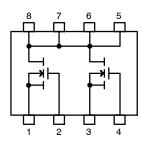


SOT-28FL / ECH8 CASE 318BF

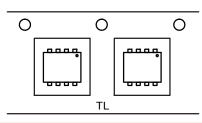
GENERIC MARKING DIAGRAM



ELECTRICAL CONNECTION



PACKING TYPE: TL



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

ECH8655R-R-TL-H

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		9	А
Drain Current (Pulse)	I _{DP}	PW ≤[]0 μs, duty cycle ≤[]%	60	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900 mm ² ×[0.8 mm) 1 unit	1.4	W
Total Dissipation	P _T	When mounted on ceramic substrate (900 $\text{mm}^2 \times 0.8 \text{ mm}$)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	24			V
Zero-Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 V,$ $V_{GS} = 0V$			1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8 V, V _{DS} = 0 V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} = 10 V, I _D = 1 mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 4.5 A	4.8	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D = 4.5 A, V _{GS} = 4.5 V	10	13	16	mΩ
	R _{DS} (on)2	I _D = 4.5 A, V _{GS} = 4.0 V	10.5	13.5	16.5	mΩ
	R _{DS} (on)3	I _D = 4.5 A, V _{GS} = 3.1 V	11	15	20	mΩ
	R _{DS} (on)4	I _D = 2 A, V _{GS} = 2.5 V	13	18	24	mΩ
Turn-ON Delay Time	t _d (on)	See specified		320		ns
Rise Time	t _r	- Test Circuit		1100		ns
Turn-OFF Delay Time	t _d (off)	1		2400		ns
Fall Time	t _f	1		2100		ns
Total Gate Charge	Qg	$V_{DS} = 10 V,$		16.8		nC
Gate-to-Source Charge	Qgs I _D = 9 A			1.6		nC
Gate-to-Drain "Miller" Charge	Qgd	1		4.8		nC
Diode Forward Voltage	V _{SD}	I _S = 9 A, V _{GS} = 0 V		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Switching Time Test Circuit

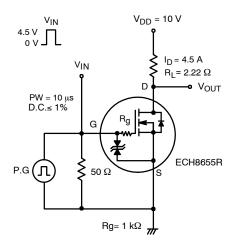


Figure 2. Switching Time Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]	Memo	
ECH8655R-R-TL-H	ECH8	3,000 pcs./reel	Pb Free and Halogen Free	

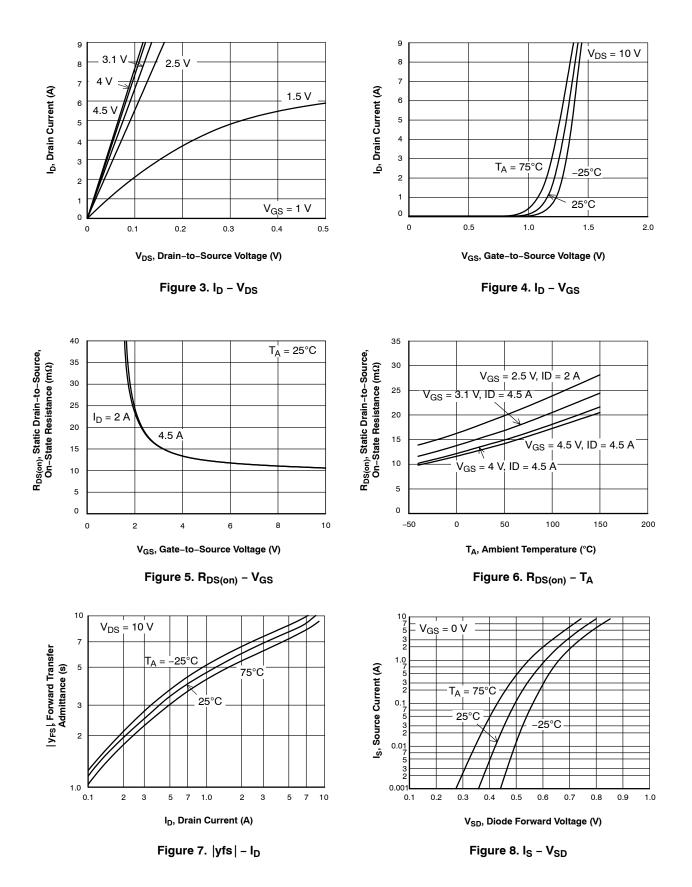
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





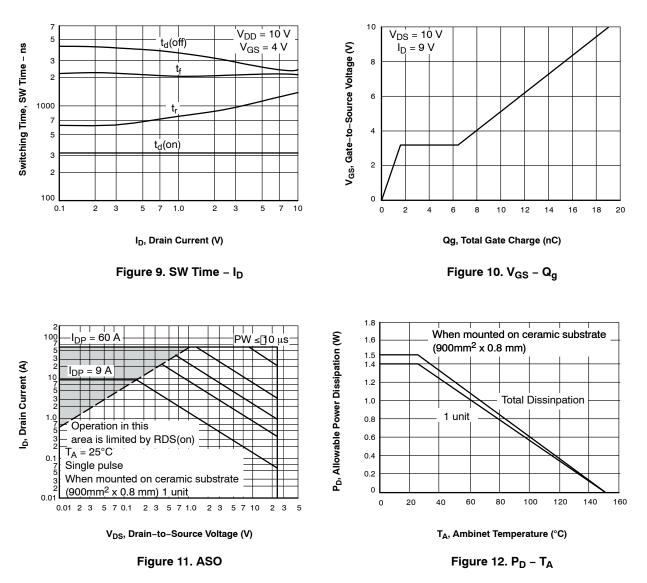
ECH8655R-R-TL-H

TYPICAL CHARACTERISTICS





ECH8655R-R-TL-H



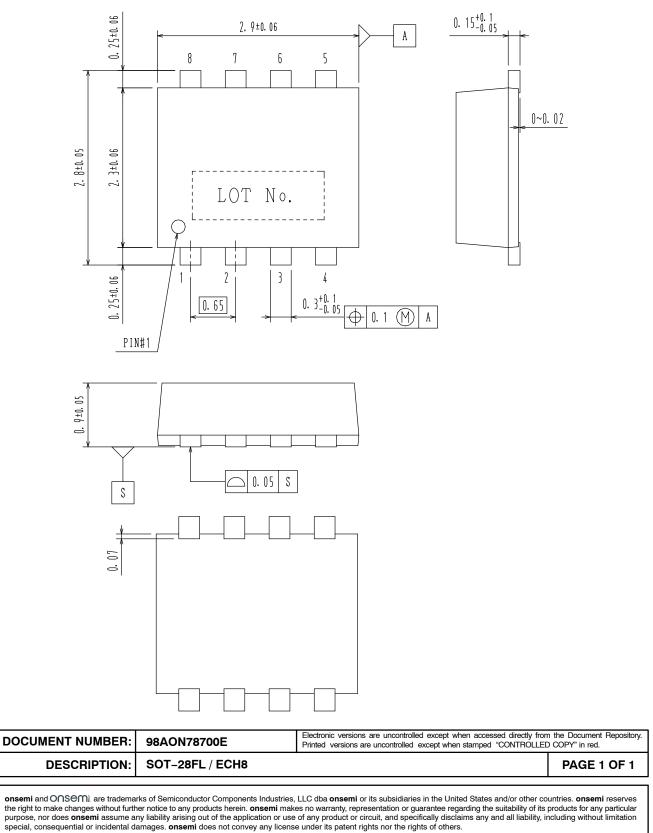
Since the ECH8655R-R-TL-H is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.





SOT-28FL / ECH8 CASE 318BF ISSUE O

DATE 31 MAR 2012



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TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>